

Silicon PNP Power Transistors

2SB1339

DESCRIPTION

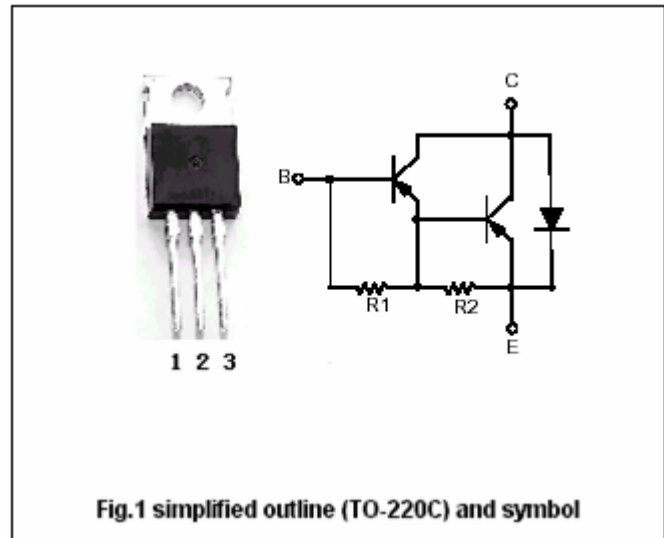
- With TO-220C package
- High DC current gain
- Low saturation voltage
- DARLINGTON

APPLICATIONS

- For low frequency power amplifier and power driver applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-120	V
V_{CEO}	Collector -emitter voltage	Open base	-120	V
V_{EBO}	Emitter-base voltage	Open collector	-6	V
I_C	Collector current		-6	A
I_{CM}	Collector current-peak		-10	A
P_C	Collector power dissipation	$T_a=25^\circ\text{C}$	2	W
		$T_C=25^\circ\text{C}$	40	
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=-5mA; I_B=0$	-120			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=-50\mu A; I_E=0$	-120			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-3A; I_B=-6mA$			-1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=-120V; I_E=0$			-100	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=-5V; I_C=0$			-3.0	mA
h_{FE}	DC current gain	$I_C=-2A; V_{CE}=-3V$	2000		20000	
f_T	Transition frequency	$I_C=-0.5A; V_{CE}=-5V$		12		MHz
C_{OB}	Output capacitance	$I_E=0; V_{CB}=-10V; f=1MHz$		70		pF

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PACKAGE OUTLINE

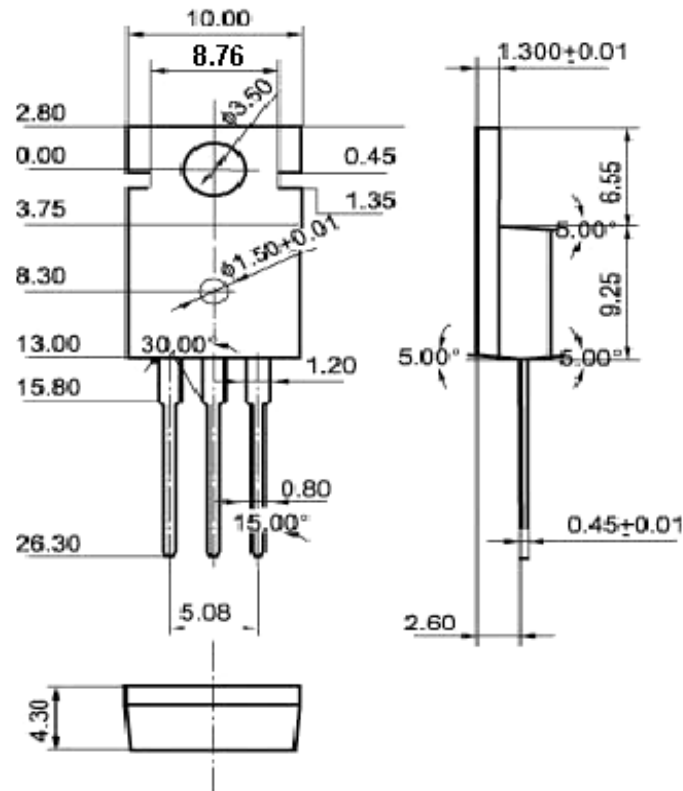


Fig.2 Outline dimensions (unindicated tolerance: ± 0.10 mm)